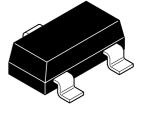


ZXTN25012EFL 12V, SOT23, NPN low power transistor

Summary

 $BV_{CEO} > 12V$ $BV_{ECO} > 4.5V$ $h_{FE} > 500$ $I_{C(cont)} = 2A$ $V_{CE(sat)} < 65 mV @ 1A$ $R_{CE(sat)} = 46 m\Omega$ $P_D = 350mW$



Description

Advanced process capability has been used to achieve high current gain hold up making this device ideal for applications requiring high pulse currents.

Features

- High peak current
- Low saturation voltage
- 6V reverse blocking voltage

Applications

- MOSFET and IGBT gate driving
- DC-DC conversion
- LED driving
- Interface between low voltage IC's and load

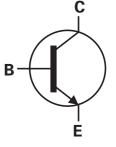
Ordering information

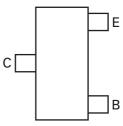
| Device | Reel size | Tape width | Quantity |
|----------------|-----------|------------|----------|
| | (inches) | (mm) | per reel |
| ZXTN25012EFLTA | 7 | 8 | 3000 |

Device marking

1B6

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Pinout - top view

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|---|-----------------------------------|-------------|-------|
| Collector-base voltage | V _{CBO} | 20 | V |
| Collector-emitter voltage | V _{CEO} | 12 | V |
| Emitter-collector voltage | V _{ECO} | 4.5 | V |
| Emitter-base voltage | V _{EBO} | 7 | V |
| Continuous collector current ^(a) | Ι _C | 2 | А |
| Base current | Ι _Β | 500 | mA |
| Peak pulse current | I _{CM} | 15 | А |
| Power dissipation @ T _{amb} =25°C ^(a) | PD | 350 | mW |
| Linear derating factor | | 2.8 | mW/°C |
| Operating and storage temperature range | T _j , T _{stg} | - 55 to 150 | °C |

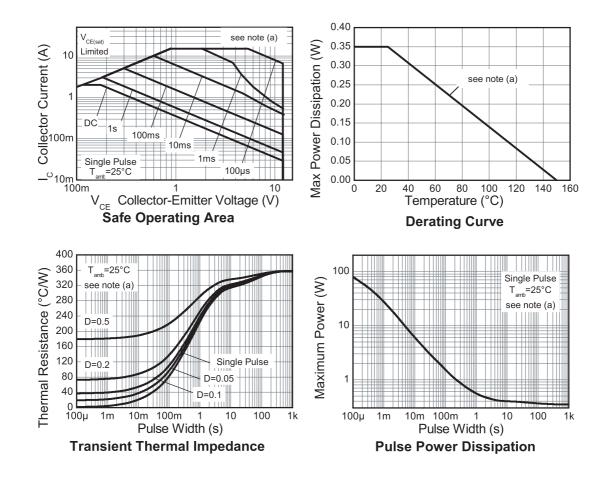
Thermal resistance

| Parameter | Symbol | Limit | Unit |
|------------------------------------|----------------|-------|------|
| Junction to ambient ^(a) | R_{\ThetaJA} | 357 | °C/W |

NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Characteristics



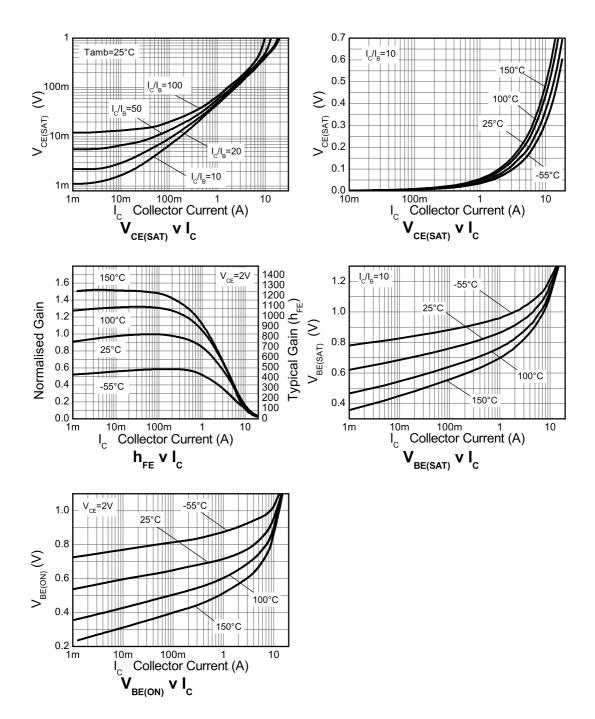
| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|----------------------|------|------|------|------|--|
| Collector-base breakdown voltage | BV _{CBO} | 20 | 40 | | V | I _C = 100μA |
| Collector-emitter breakdown voltage | BV _{CEO} | 12 | 17 | | V | I _C = 10mA ^(*) |
| Emitter-base breakdown voltage | BV _{EBO} | 7 | 8.3 | | V | I _E = 100μA |
| Emitter-collector breakdown voltage (reverse blocking) | BV _{ECX} | 6 | 8 | | V | $I_{E} = 100 \mu A, R_{BC} \le 1 k \Omega \text{ or}$ 0.25v > V_{BC} > -0.25V |
| Emitter-collector breakdown voltage (base open) | BV _{ECO} | 4.5 | 5.5 | | V | I _E = 100μA, |
| Collector cut-off current | I _{CBO} | | <1 | 50 | nA | V _{CB} = 16V |
| | | | | 20 | μA | $V_{CB} = 16V, T_{amb} = 100^{\circ}C$ |
| Emitter-base cut-off current | I _{EBO} | | <1 | 50 | nA | V _{EB} = 5.6V |
| Collector-emitter saturation | V _{CE(sat)} | | 50 | 65 | mV | I _C = 1A, I _B = 100mA ^(*) |
| voltage | | | 70 | 85 | mV | $I_{C} = 1A, I_{B} = 10mA^{(*)}$ |
| | | | 105 | 130 | mV | I _C = 2A, I _B = 40mA ^(*) |
| | | | 235 | 300 | mV | l _C = 5A, l _B = 100mA ^(*) |
| Base-emitter saturation voltage | V _{BE(sat)} | | 830 | 950 | mV | $I_{C} = 2A, I_{B} = 40mA^{(*)}$ |
| Base-emitter turn-on voltage | V _{BE(on)} | | 745 | 850 | mV | $I_{C} = 2A, V_{CE} = 2V^{(*)}$ |
| Static forward current transfer | h _{FE} | 500 | 800 | 1500 | | $I_{C} = 10 \text{mA}, V_{CE} = 2V^{(*)}$ |
| ratio | | 500 | 700 | | | $I_{C} = 1A, V_{CE} = 2V^{(*)}$ |
| | | 370 | 575 | | | $I_{C} = 2A, V_{CE} = 2V^{(*)}$ |
| | | 210 | 335 | | | $I_{C} = 5A, V_{CE} = 2V^{(*)}$ |
| | | 30 | 55 | | | $I_{C} = 15A, V_{CE} = 2V^{(*)}$ |
| Transition frequency | f _T | | 260 | | MHz | I _C = 50mA, V _{CE} = 10V f = 100MHz |
| Output capacitance | C _{obo} | | 25 | 35 | pF | V _{CB} = 10V, f = 1MHz ^(*) |
| Delay time | t _(d) | | 71 | | ns | V _{CC} = 10V |
| Rise time | t _(r) | | 70 | | ns | I _C = 1A, I _{B1} = I _{B2} = 10mA |
| Storage time | t _(s) | | 233 | | ns | איין אין אין אין אין אוואז אוואז און אין |
| Fall time | t _(f) | | 72 | | ns | |

Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

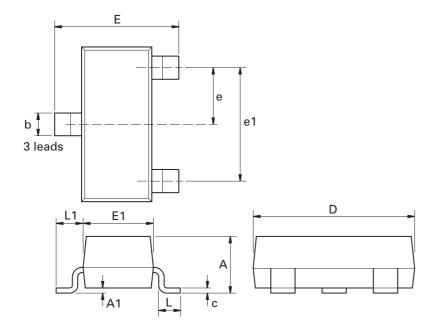
NOTES:

(*) Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%.

Typical characteristics



Package outline - SOT23



| Dim. | Millin | neters | Inches | | Dim. Milli | | neters | Inches | |
|------|--------|--------|--------|-------|------------|------|--------|--------|-------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Max. | Max. |
| А | - | 1.12 | - | 0.044 | e1 | 1.90 | NOM | 0.075 | NOM |
| A1 | 0.01 | 0.10 | 0.0004 | 0.004 | E | 2.10 | 2.64 | 0.083 | 0.104 |
| b | 0.30 | 0.50 | 0.012 | 0.020 | E1 | 1.20 | 1.40 | 0.047 | 0.055 |
| С | 0.085 | 0.120 | 0.003 | 0.008 | L | 0.25 | 0.62 | 0.018 | 0.024 |
| D | 2.80 | 3.04 | 0.110 | 0.120 | L1 | 0.45 | 0.62 | 0.018 | 0.024 |
| е | 0.95 | NOM | 0.0375 | NOM | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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| Europe | Americas | Asia Pacific | Corporate Headquarters |
|---|---|--|--|
| Zetex GmbH Kustermann-park Balanstraße 59 D-81541 München Germanv | Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA | Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong | Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom |
| Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com | Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com | Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com | Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com |

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